



# STY60NM50

## N-CHANNEL 500V - 0.045Ω - 60A Max247 Zener-Protected MDmesh™ Power MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STY60NM50	500V	< 0.05Ω	60 A

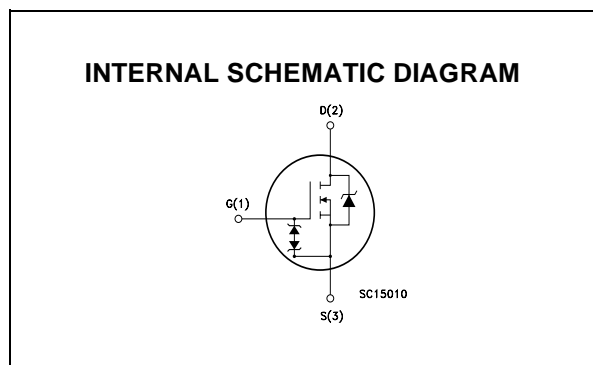
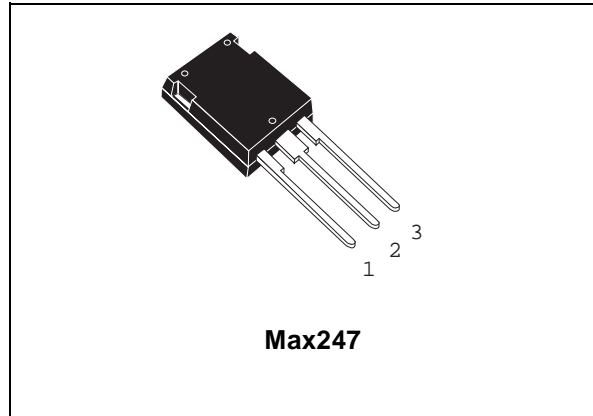
- TYPICAL R<sub>DS(on)</sub> = 0.045Ω
- HIGH dv/dt AND AVALANCHE CAPABILITIES
- IMPROVED ESD CAPABILITY
- LOW INPUT CAPACITANCE AND GATE CHARGE
- LOW GATE INPUT RESISTANCE
- TIGHT PROCESS CONTROL
- INDUSTRY'S LOWEST ON-RESISTANCE

### DESCRIPTION

The MDmesh™ is a new revolutionary MOSFET technology that associates the Multiple Drain process with the Company's PowerMESH™ horizontal layout. The resulting product has an outstanding low on-resistance, impressively high dv/dt and excellent avalanche characteristics. The adoption of the Company's proprietary strip technique yields overall dynamic performance that is significantly better than that of similar competition's products.

### APPLICATIONS

The MDmesh™ family is very suitable for increasing power density of high voltage converters allowing system miniaturization and higher efficiencies.



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	500	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	500	V
V <sub>GS</sub>	Gate- source Voltage	±30	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 25°C	60	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	37.8	A
I <sub>DM</sub> (•)	Drain Current (pulsed)	240	A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	560	W
V <sub>ESD(G-S)</sub>	Gate source ESD(HBM-C=100pF, R=15KΩ)	6	KV
	Derating Factor	4.5	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	15	V/ns
T <sub>stg</sub>	Storage Temperature	-65 to 150	°C
T <sub>j</sub>	Max. Operating Junction Temperature	150	°C

(•) Pulse width limited by safe operating area  
November 2003

(1) I<sub>SD</sub> ≤ 60A, di/dt ≤ 400A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>

# STY60NM50

## THERMAL DATA

Rthj-case	Thermal Resistance Junction-case	Max	0.22	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	30	°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose		300	°C

## AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max)	30	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 35 V)	1.4	J

## ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED) OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	500			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating, T <sub>C</sub> = 125 °C			10 100	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20V			± 10	μA

## ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	3	4	5	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 30A		0.045	0.05	Ω

## DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (1)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> , I <sub>D</sub> = 30A		35		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> = 0		7500		pF
C <sub>oss</sub>	Output Capacitance			980		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			200		pF
R <sub>G</sub>	Gate Input Resistance	f=1 MHz Gate DC Bias = 0 Test Signal Level = 20mV Open Drain		1.5		Ω

Note: 1. Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %.

**ELECTRICAL CHARACTERISTICS (CONTINUED)**  
SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 250V, I_D = 30A$		51		ns
$t_r$	Rise Time	$R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 3)		58		ns
$Q_g$	Total Gate Charge	$V_{DD} = 400V, I_D = 60A,$ $V_{GS} = 10V$		190	266	nC
$Q_{gs}$	Gate-Source Charge			53		nC
$Q_{gd}$	Gate-Drain Charge			97		nC

SWITCHING OFF

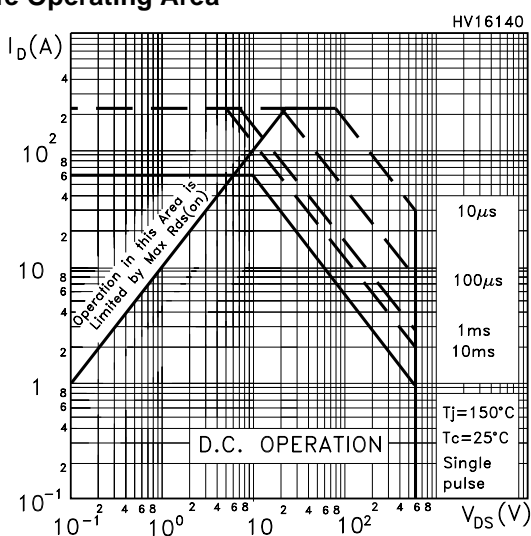
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 400V, I_D = 60A,$		51		ns
$t_f$	Fall Time	$R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 5)		46		ns
$t_c$	Cross-over Time			108		ns

SOURCE DRAIN DIODE

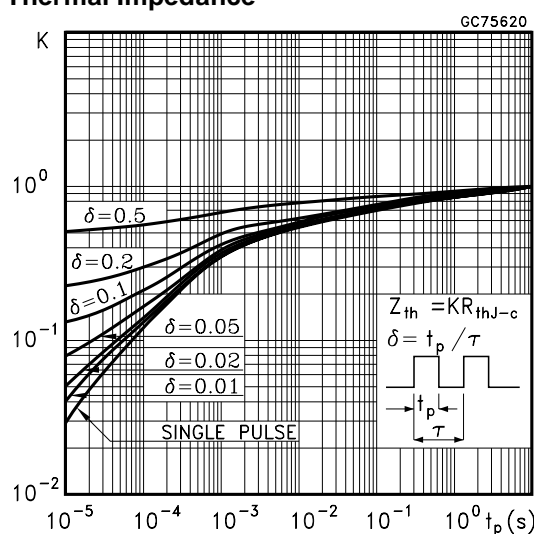
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				60	A
$I_{SDM(2)}$	Source-drain Current (pulsed)				240	A
$V_{SD(1)}$	Forward On Voltage	$I_{SD} = 60A, V_{GS} = 0$			1.5	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 60A, di/dt = 100A/\mu s,$		532		ns
$Q_{rr}$	Reverse Recovery Charge	$V_{DD} = 100V, T_j = 25^\circ C$		9.9		$\mu C$
$I_{RRM}$	Reverse Recovery Current	(see test circuit, Figure 5)		37		A
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 60A, di/dt = 100A/\mu s,$		636		ns
$Q_{rr}$	Reverse Recovery Charge	$V_{DD} = 100V, T_j = 150^\circ C$		13.4		$\mu C$
$I_{RRM}$	Reverse Recovery Current	(see test circuit, Figure 5)		42		A

Note: 1. Pulsed: Pulse duration = 300  $\mu s$ , duty cycle 1.5 %.  
2. Pulse width limited by safe operating area.

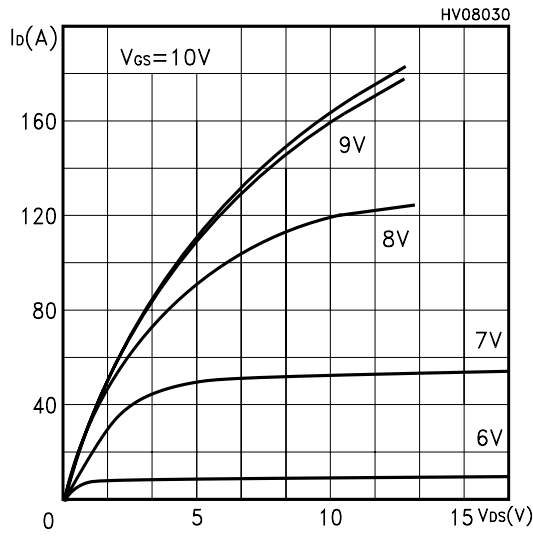
**Safe Operating Area**



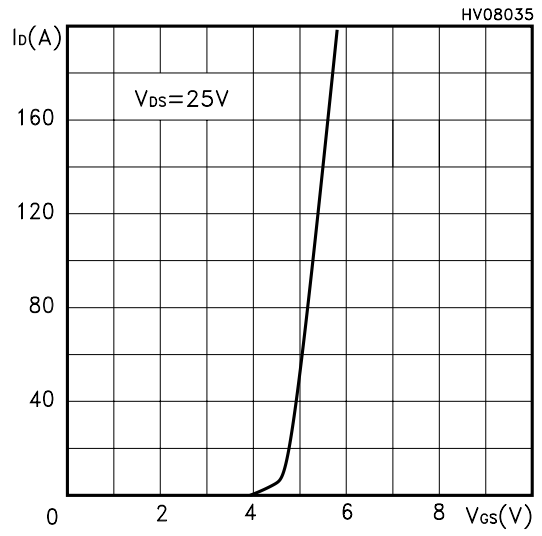
**Thermal Impedance**



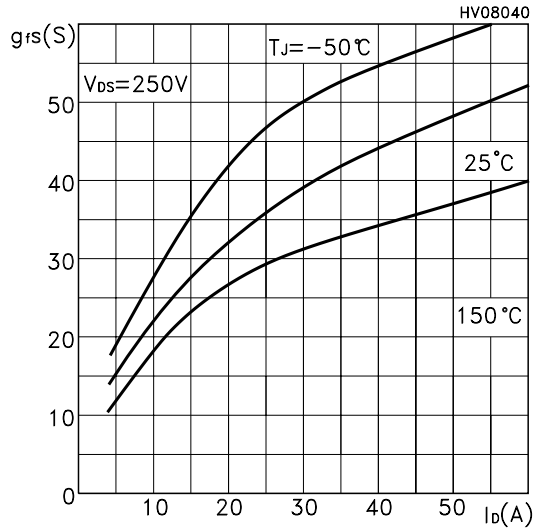
**Output Characteristics**



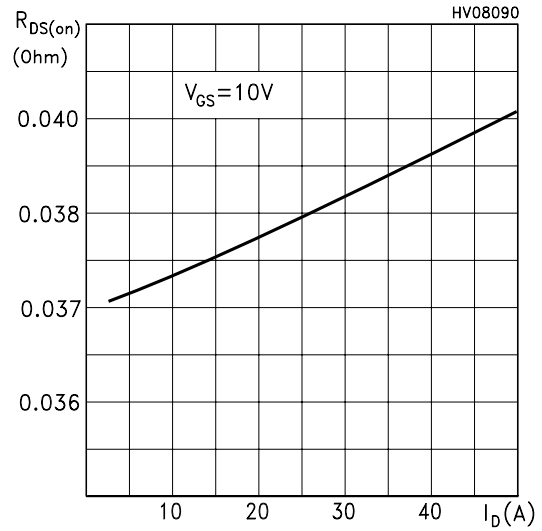
**Transfer Characteristics**



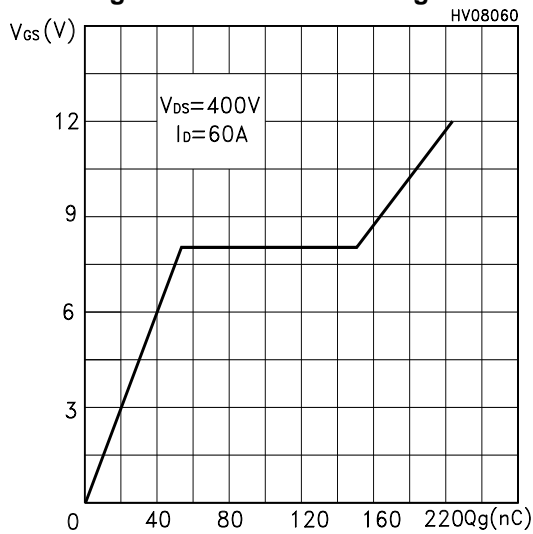
**Transconductance**



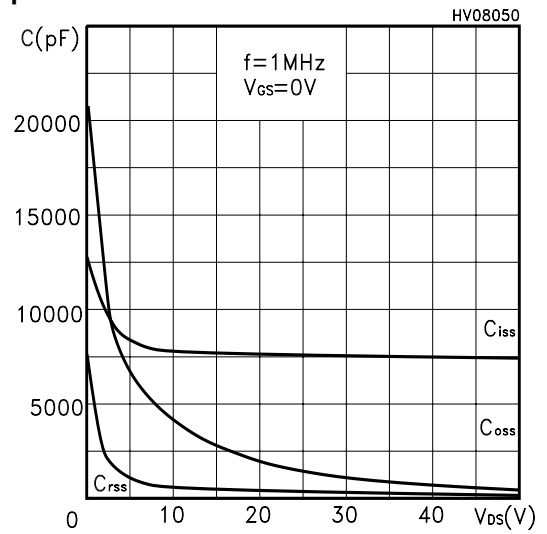
**Static Drain-source On Resistance**



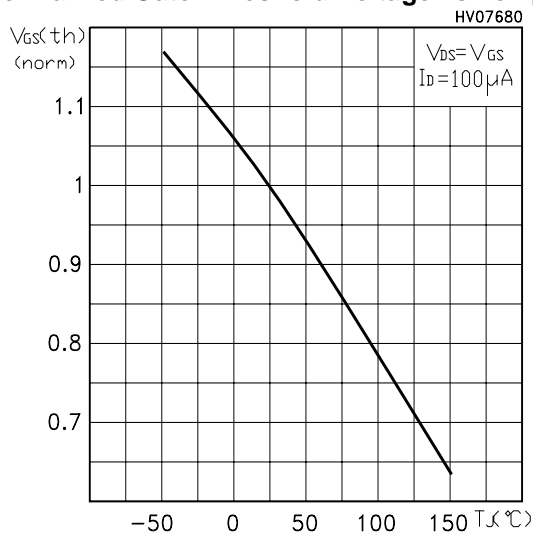
**Gate Charge vs Gate-source Voltage**



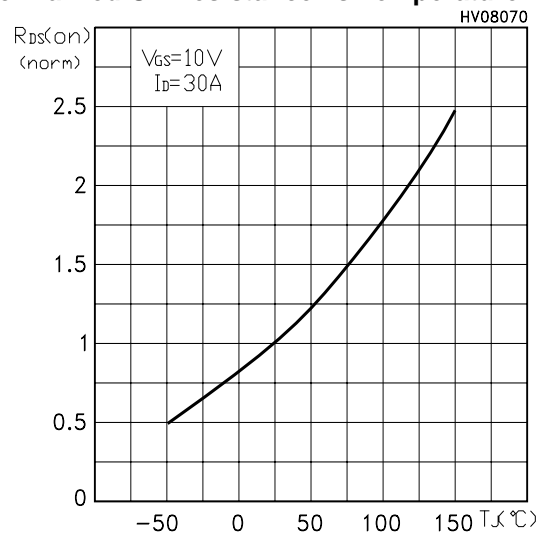
**Capacitance Variations**



Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

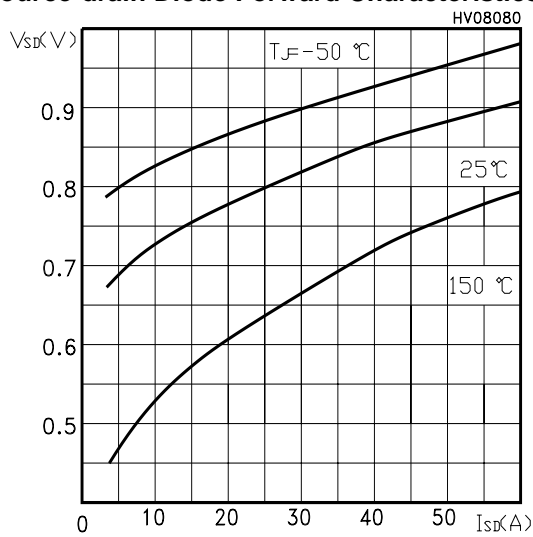


Fig. 1: Unclamped Inductive Load Test Circuit

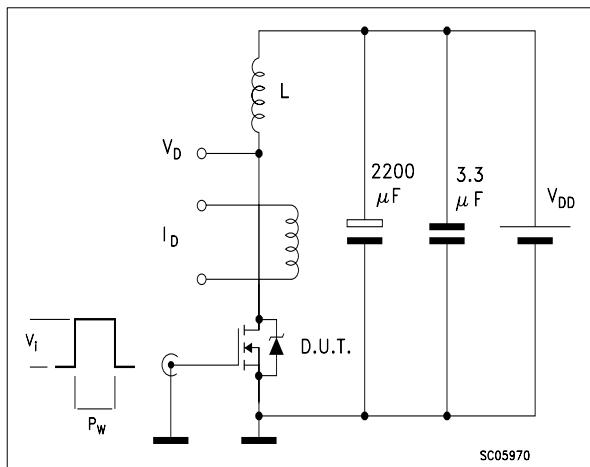


Fig. 2: Unclamped Inductive Waveform

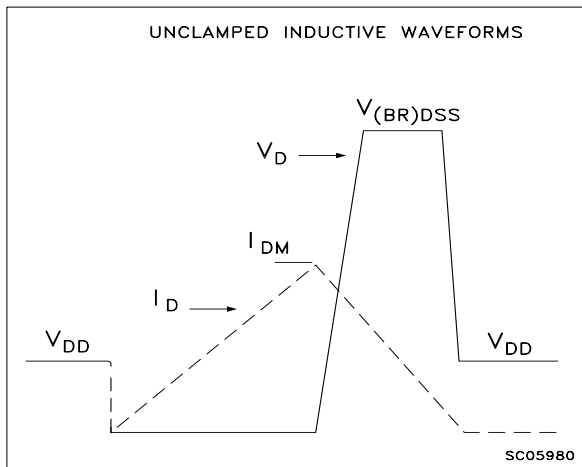


Fig. 3: Switching Times Test Circuit For Resistive Load

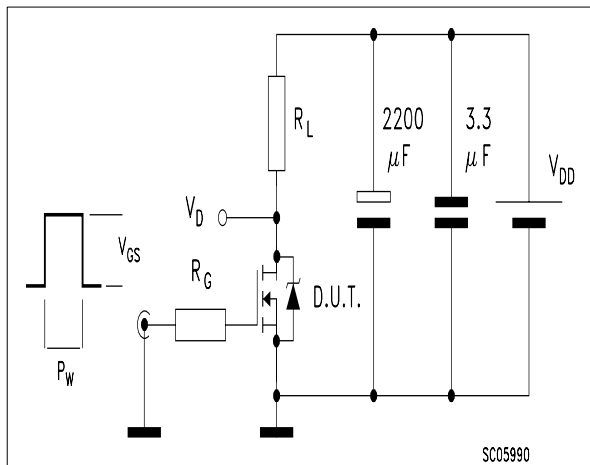


Fig. 4: Gate Charge test Circuit

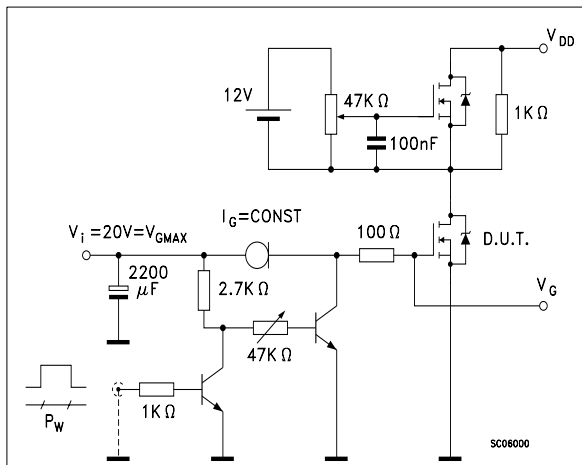
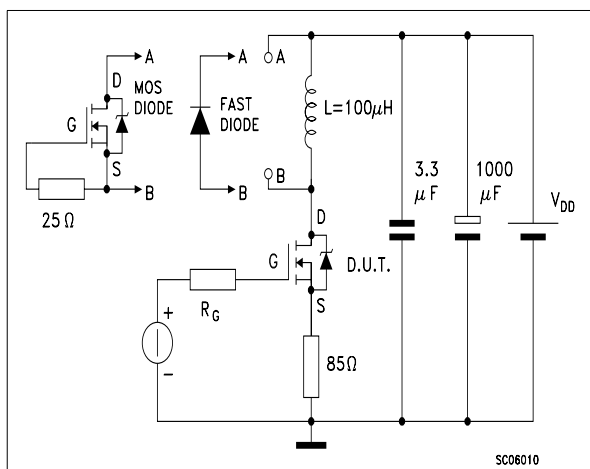
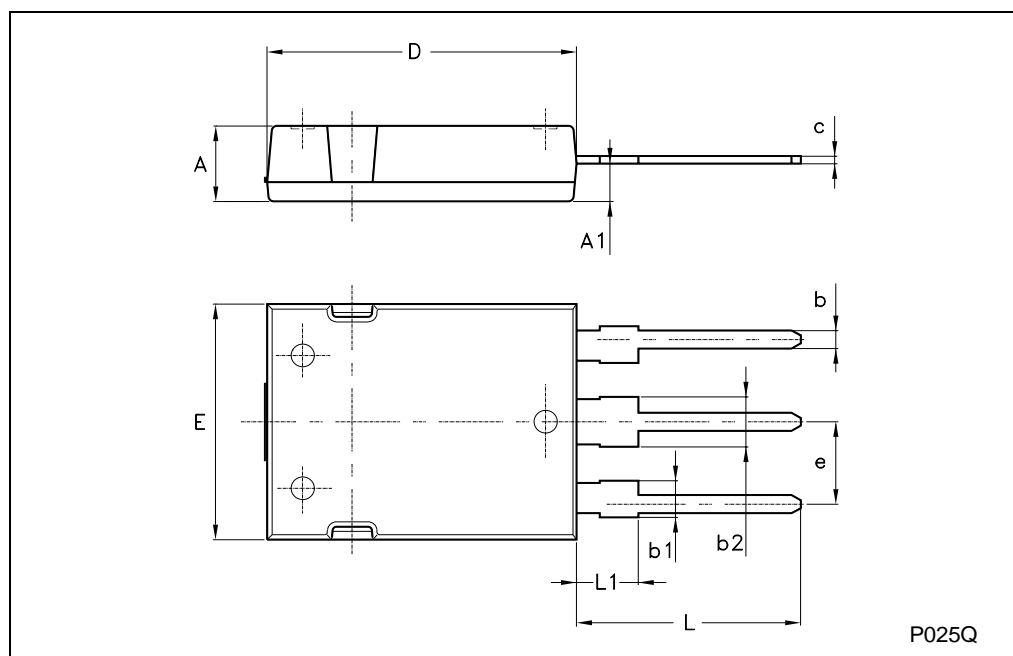


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



Max247 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.70		5.30			
A1	2.20		2.60			
b	1.00		1.40			
b1	2.00		2.40			
b2	3.00		3.40			
c	0.40		0.80			
D	19.70		20.30			
e	5.35		5.55			
E	15.30		15.90			
L	14.20		15.20			
L1	3.70		4.30			



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